Pyrazino[2,3-g]quinoxaline-2,7-dione based π -conjugated polymers with affinity towards acids and semiconductor performance in organic thin film transistors

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Additional data



Fig. S1 The optimized geometry and dihedral angles of the **PQx2T-BT-Me** dimer using Gaussian 09 Revision $D.01^1$ with the B3LYP/6-31G(d) level of theory under tight convergence.



Fig. S2 The optimized LUMO and HOMO wavefunction distributions of the **PQx2T-BT-Me** dimer using Gaussian 09 Revision $D.01^1$ with the B3LYP/6-31G(d) level of theory under tight convergence.



Fig. S3 The optimized geometry and dihedral angles of the **PQx2T-TT-Me** dimer using Gaussian 09 Revision $D.01^1$ with the B3LYP/6-31G(d) level of theory under tight convergence.



PQx2T-TT-Me dimer

Fig. S4 The optimized LUMO and HOMO wavefunction distributions of the **PQx2T-TT-Me** dimer using Gaussian 09 Revision $D.01^1$ with the B3LYP/6-31G(d) level of theory under tight convergence.



Fig. S5 300 MHz ¹H NMR spectrum for 1,6-bis(2-decyltetradecyl)-3,8-di(thiophen-2-yl)-1,6-dihydropyrazino[2,3-g]quinoxaline-2,7-dione (**PQx2T-24**) in CDCl₃.



Fig. S6 75 MHz ¹³C NMR spectrum for 1,6-bis(2-decyltetradecyl)-3,8-di(thiophen-2-yl)-1,6-dihydropyrazino[2,3-*g*]quinoxaline-2,7-dione (**PQx2T-24**) in CDCl₃.



Fig. S7 The MS (ESI+) [M+H]+ spectra for 1,6-bis(2-decyltetradecyl)-3,8-di(thiophen-2-yl)-1,6-dihydropyrazino[2,3-*g*]quinoxaline-2,7-dione (**PQx2T-24**).





Fig. S9 75 MHz ¹³C NMR spectrum for 3,8-bis(5-bromothiophen-2-yl)-1,6-bis(2-decyltetradecyl)-1,6-dihydropyrazino[2,3-*g*]quinoxaline-2,7-dione (**PQx2T-Br-24**) in CDCl₃.



Fig. S10 The HR-MS (ESI+) (M+H)+ spectra for 3,8-bis(5-bromothiophen-2-yl)-1,6-bis(2-decyltetradecyl)-1,6-dihydropyrazino[2,3-g]quinoxaline-2,7-dione (**PQx2T-Br-24**).



Fig. S11 Cyclic voltammograms of polymers in a 0.1 M tetrabutylammonium hexafluorophosphate solution under nitrogen in dry acetonitrile at a scan rate of 50 mV s⁻¹.



 $\begin{array}{c} {}_{13.0 \ 12.5 \ 12.0 \ 11.5 \ 11.0 \ 10.5 \ 10.0 \ 9.5 \ 9.0 \ 8.5 \ 8.0 \ 7.5 \ 7.0 \ 6.5 \ 6.0 \ 5.5 \ 5.0 \ 4.5 \ 4.0 \ 3.5 \ 3.0 \ 2.5 \ 2.0 \ 1.5 \ 1.0 \ 0.5 \ 0.0 \ -0.5 \ -1 \ f1 \ (ppm) \ Fig. S12 \ 300 \ MHz \ ^1H \ NMR \ spectrum \ for \ PPQx2T-BT-24 \ in \ CDCl_3. \end{array}$



13.0 12.5 12.0 11.5 11.0 10.5 10.0 9.5 9.0 8.5 8.0 7.5 7.0 6.5 6.0 5.5 5.0 4.5 4.0 3.5 3.0 2.5 2.0 1.5 1.0 0.5 0.0 -0.5 -1 **Fig. S13** 300 MHz ¹H NMR spectrum for **PPQx2T-TT-24** in CDCl₃.



Fig. S14 High temperature GPC traces of PPQx2T-BT-24 with refractive index detector.



Fig. S15 High temperature GPC traces of PPQx2T-TT-24 with refractive index detector.



Fig. S16 TGA curves of **PPQx2T-BT-24** and **PPQx2T-TT-24** with a heating rate of 10 °C min⁻¹ under nitrogen.



Fig. S17 DSC thermogram of PPQx2T-BT-24 at a heating rate of 20 °C min⁻¹ under nitrogen.



Fig. S18 DSC thermogram of PPQx2T-TT-24 at a heating rate of 20 °C min⁻¹ under nitrogen.



Fig. S19 XRD diagram obtained in the reflection mode for the spin-coated **PPQx2T-BT-24** thin film on silicon substrates annealed at 100, 150, 200, and 250 °C.



Fig. S20 XRD diagram obtained in the reflection mode for the spin-coated **PPQx2T-TT-24** thin film on silicon substrates annealed at 100, 150, 200, and 250 °C.



Fig. S21 XRD diagrams obtained in the transmission mode for PPQx2T-BT-24 and PPQx2T-TT-24 polymer flakes.



Fig. S22 The transfer (left) and output curves (right) of a typical OTFT device with a **PPQx2T-TT-24** thin film annealed at 200 °C. Device dimensions: channel width (W) = 1000 µm; channel length (L) = 30 µm.

Table S1 The summary of OTFT performance of PPQx2T-BT-24 and PPQx2T-TT-24.

Polymer	Annealing	Hole mobility ^a (10 ⁻³	Electron mobility ^a	Average V _{th}	I_{on}/I_{off}^{b}
	temperature	$cm^2V^{-1}s^{-1}$)	$(10^{-3} \text{ cm}^2 \text{V}^{-1} \text{s}^{-1})$	(V)	
	(°C)			p-/n-channel	
	100	$0.42~(0.38\pm0.03)$	$4.62~(3.99\pm 0.46)$	-23.06/44.12	~10 ²
PPQx2T-	150	$0.47~(0.48\pm0.02)$	$4.47~(3.94\pm 0.40)$	-25.63/49.68	~10 ²
BT-24	200	$0.52~(0.50\pm 0.02)$	$4.28~(3.97\pm0.31)$	-30.47/42.42	~10 ²
	250	$0.31~(0.28\pm 0.03)$	$2.84~(2.62\pm 0.25)$	-50.49/43.48	~10 ²
	100	$16.20(12.90 \pm 1.89)$	$0.14~(0.12\pm0.05)$	-23.83/79.48	~10 ⁵
PPQx2T-	150	$42.00(34.10\pm5.46)$	$2.95~(2.81\pm0.20)$	-19.45/66.36	~10 ⁵
TT-24	200	$48.20~(37.90\pm 6.75)$	$3.95~(3.12\pm0.98)$	-20.29/62.63	~10 ⁵
	250	$36.60(27.30 \pm 6.53)$	$2.09(1.30 \pm 0.58)$	-22.14/63.11	~10 ⁵

^a The maximum (average ± standard deviation) mobility was calculated from the saturated regime of at least five devices for each condition. ^b Only p-channel data are reported for **PPQx2T-TT-24**.

Polymer	TFA		BBr ₃	
-	Conc.	λ_{max} , nm	Conc.	λ_{max} , nm
	0	600	0	600
	1 mM	600	1 µM	605
	10 mM	602		
DDA9T DT 94	50 mM	604		
PPQX21-B1-24	100 mM	607		
	500 mM	818(sh)		
	1 M	834		
	2 M	846	4 μΜ	621(sh)
	0	627	0	627
	1 mM	626	1 µM	768(sh)
	5 mM	617		
	10 mM	615		
PPQx2T-TT-24	50 mM	786		
	100 mM	804		
	500 mM	896		
	1 M	908		
	2 M	914	6 µM	846

Table S2 The summary of UV-Vis absorption of various acids for PPQx2T-BT-24 and PPQx2T-TT-24.

References

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